

328812 (28)

BE (8th Semester)

Examination, April - May, 2021

Branch : Et & T

VLSI DESIGN

Time Allowed : Three Hours

Maximum Marks : 80

Minimum Pass Marks : 28

Note : Part (a) of each unit is compulsory. Attempt any two parts from (b), (c) and (d).

UNIT - I

- Q. 1.** (a) What is SSI, MSI and VLSI. **2**
- (b) Explain VLSI Design Flow using flow chart. **7**

(2)

(c) Explain design hierarchy concept of regularity modularity and locality. 7

(d) Write short notes on FPGA and Design 7

$F = \bar{x}_1\bar{x}_2 + x_1x_2$ using two input LUT.

UNIT - II

Q. 2. (a) Draw the circuit diagram of CMOS inverter. 2

(b) Explain basic steps of fabrication process of CMOS. 7

(c) Design circuit diagram and layout of 3 Input NAND gate. 7

(d) Draw basic BiCMOS circuit of two input NAND gate. 7

(3)

UNIT - III

- Q. 3. (a) What is the difference between SRAM and DRAM. 2
- (b) Draw circuit diagram of 4×4 MOS NOR ROM and explain storage in each location. 7
- (c) Design schematic of 4×1 MUX. 7
- (d) Draw schematic and layout of 6 transistor SRAM cell. 7

UNIT - IV

- Q. 4. (a) What is entity in VHDL. 2
- (b) Write short notes on process statement and write down VHDL code of 4×1 MUX. 7
- (c) Explain in brief structural style of modelling with one example. 7

(4)

- (d) Write VHDL code for 9 Bit Parity generator circuits. 7

UNIT - V

- Q. 5. (a) What is FSM. 2
- (b) What is the difference between Melay & Moore State Machine. 7
- (c) Write short note on operator overloading. 7
- (d) Design an FSM that has input w and an output z. The machine is a sequence detector that produces $z = 1$ when the previous two values of w were 00 or 11, otherwise $z = 0$. 7